

U.S. UTILITY Pat nt Application

PATENT NUMBER and ISSUE DATE

APPL NUM 10047323 01/14/2002 427 00 1762 SUBCLASS GAU 1762 SUP 176	_	MESSA TON	1				<u> </u>		
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**APPLICANTS: Lampert William; Eiting Christopher; Smith Scott; Haas Trice; **CONTINUING DATA VERIFIED: THIS APPLN CLAIMS BENEFIT OF 60/265, 167 01/30/2001 **FOREIGN APPLICATIONS VERIFIED: PG-PUB DO NOT PUBLISH RESCIND	186	10047323	01/14/2002	427 -	104	1762	Song		
PG-PUB DO NOT PUBLISH RESCIND Foreign priority claimed yes no 35 USC 119 conditions met Verified and Acknowledged Examiners's initials TITLE: Method of growing homoepitaxial silicon carbide US DEPT. OF COMM. PAT & TM. PTO 436L(Rev 12-94) DTICE OF ALLOWANCE MAILED Total Claims ALLOWED Total Claims ALLOWED Frint Claim for.		**APPLICANT	APPLICANTS: Lampert William; Eiting Christopher; Smith Scott; Haas Trice; *CONTINUING DATA VERIFIED:						
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TERMINAL	Primary Examiner PREPARED FOR ISSUE	Application Examiner				
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